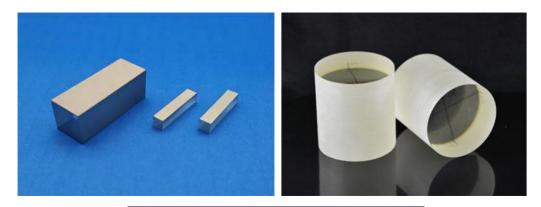


# LiNbO3 crystals for EO applications

- Preferably for Er:YAG-, Ho:YAG-, Tm:YAG laser
- Wavelengths up to 3µm
- Brewster for laser with low amplification

LiNbO3 crystals have become one of the most commonly used material for Q-switches and phase modulators for its high EO coefficients, with an electric field applied transverse to the direction of light propagation, LiNBO3 cells can be configured to operate at a lower voltage than comparable KD\*P cells. LiNbO3 can also be a good choice for infrared wavelengths as long as 3.0 µm. Hangzhou Shalom EO offers the polished, and AR coating and Au-Cr electroded **LiNbO3 crystals** used in pockels cells.





#### **Modules or types**

#### A variety types of crystals are available upon your request:

- Crystal boules with inspection polishing
- Crystal blanks with inspection polishing
- Crystals with laser grade polishing
- Crystals with AR coating and Cr-Au electrode

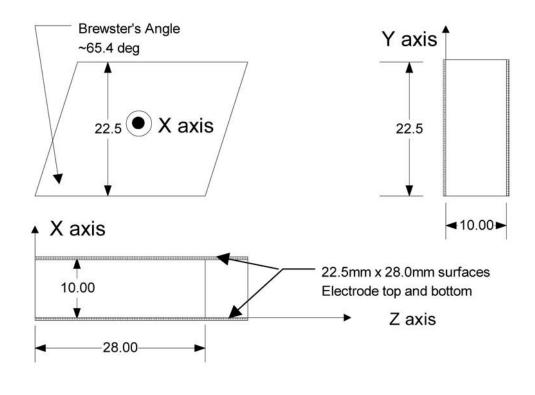


### **SPECIFICATIONS**

Specification of LiNbO3 crystals for pockels cells applications		
Crystal materials	LiNbO3 crystals	
Size	Customized	
Size tolerance	+/-0.1mm	
Length tolerance	+/-0.2mm	
Surface quality	20/10 S/D	
Parallelism	<20 arc seconds	
Flatness	< Lambda/10 @633nm	
Chamfer	0.1-0.3mmx45°	
Chips	<0.15mm	
Side surface	Fine ground	
Orientation tolerance	< 10 arc minutes	
Wavefront distortion	<lambda 4@633nm<="" td=""></lambda>	
Extinction ratio	>200:1	
Coating	AR/AR@1064nm or customized	
Damaging threshold	>100mW/cm^2@1064nm 10nS 10Hz pulse	
Electrode on side surface	Chrome gold electrode (Cr+Au)	

Note: crystals with other special specificaton is available upon request

#### Example: LiNbO3 crystals with bruster angle





## Hangzhou Shalom Electro-optics Technology Co., Ltd.

Basic Properties		
Crystal Structure	Trigonal, space group R3c	
Cell Parameters	a = 0.515, c = 13.863, Z = 6	
Melting Point	1255±5oC	
Curie Point	1140±5oC	
Mohs Hardness	5	
Density	4.64 g/cm3	
Absorption Coefficient	~ 0.1%/cm @ 1064 nm	
Solubility	insoluble in H2O	
Relative Dielectric Constant	e <sup>T</sup> <sub>11</sub> /e <sub>0</sub> : 85	
	e <sup>T</sup> <sub>33</sub> /e <sub>0</sub> : 29.5	
Thermal Expansion Coefficients(@	a, 2.0 x 10 <sup>-6</sup> /K   c, 2.2 x 10 <sup>-6</sup> /K	
25oC)	a, 2.0 X 10 /K   C, 2.2 X 10 /K	
Thermal Conductivity	38 W /m /K @ 25oC	

Linear Optical Properties		
Transparency Range	420-5200nm	
Refractive Indices	ne=2.146, no = 2.220 @ 1300 nm	
	ne= 2.156, no = 2.232 @ 1064 nm	
	ne= 2.203, no = 2.286 @ 632.8nm	
Optical Homogeneity	~ 5 x 10 <sup>-5</sup> /cm	
Sellmeier Equations	$n^{2}o(l) = 4.9048 + 0.11768/(l^{2} - 0.04750) - 0.027169l^{2}$	
(I in mm)	$n^2e(l) = 4.5820 + 0.099169/(l^2 - 0.04443) - 0.021950l^2$	

Nonlinear Optical Properties		
NLO Coefficients	d33 = 34.4 pm/V	
	d31 = d15 = 5.95 pm/V	
	d22 = 3.07 pm/V	
Efficiency NLO Coefficients	deff =5.7 pm/V or ~14.6 x d36 (KDP)	
	for frequency doubling 1300 nm	
	deff =5.3 pm/V or $\sim$ 13.6 x d <sub>36</sub> (KDP)	
	for OPO pumped at 1064 nm	
	deff =17.6 pm/V or $\sim$ 45 x d <sub>36</sub> (KDP)	
	for quasi-phase-matched structure	
Electro-Optic Coefficients	$g^{T}33 = 32 \text{ pm/V}, g^{S}33 = 31 \text{ pm/V}$	
	g <sup>T</sup> 31 = 10 pm/V, g <sup>S</sup> 31=8.6 pm/V	
	g <sup>T</sup> 22 = 6.8 pm/V, g <sup>S</sup> 22= 3.4 pm/V	
Half-Wave Voltage, DC	3.03 KV 4.02 KV	
Electrical field  z, light ^z		
Electrical field  x or y, light  z		



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